Effects of arsenic oxides on GaAs surfaces on photoluminescence properties of buried InGaAs quantum wells: Dependence on initial surfaces before oxidation

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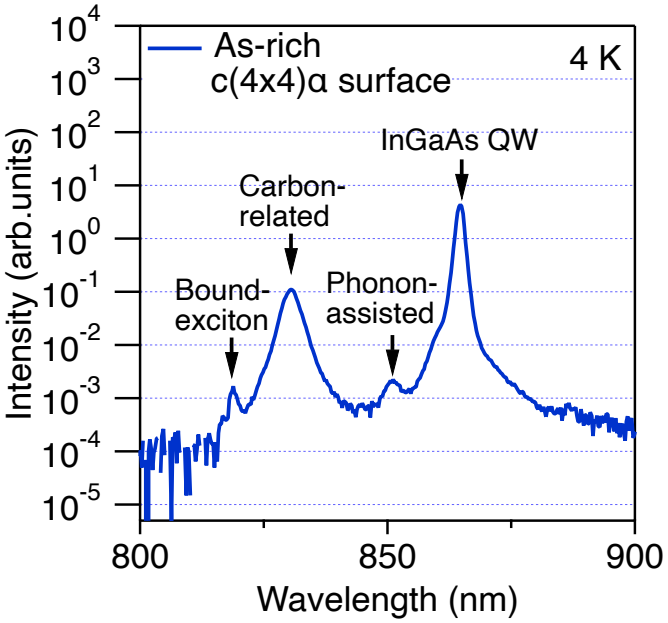
This is a supplementary material of the above-named article, which will be published in *Journal of Applied Physics*. It contains an additional figure of the low-temperature PL spectrum with a logarithmic intensity scale, where each emission peak was identified.



Supplementary Figure 1. Low-temperature PL spectra of As-rich c(4×4)α sample for a spectral region from 800 to 900 nm. We attribute peaks at 820 and 830 nm to the bound-exciton and carbon related lines of GaAs, respectively, and a small peak at 850 nm to the phonon-assisted line. The peak at 865 nm is thus attributed to the InGaAs QW.